

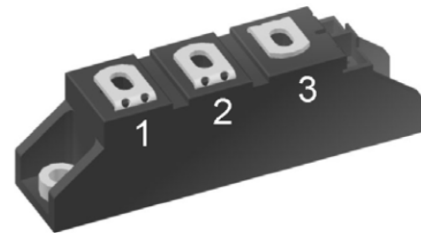
Standard Rectifier Module

$$V_{RRM} = 2 \times 1200V$$

$$I_{FAV} = 120A$$

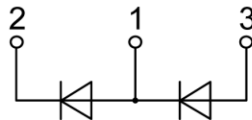
$$V_F = 1.13V$$

Phase leg



Backside: isolated

 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

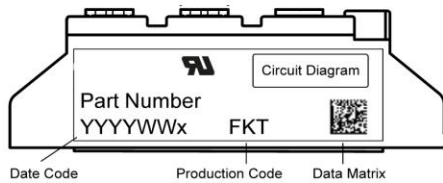
- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: TO-240AA

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Rectifier				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$			1300	V	
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200	V	
I_R	reverse current	$V_R = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		200	μA	
		$V_R = 1200\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$		15	mA	
V_F	forward voltage drop	$I_F = 150\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$		1.20	V	
			$T_{VJ} = 125^{\circ}\text{C}$		1.43	V	
		$I_F = 300\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$		1.13	V	
			$T_{VJ} = 125^{\circ}\text{C}$		1.46	V	
I_{FAV}	average forward current	$T_C = 100^{\circ}\text{C}$	$T_{VJ} = 150^{\circ}\text{C}$		120	A	
$I_{F(RMS)}$	RMS forward current	180° sine			180	A	
V_{FO}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}\text{C}$		0.75	V	
r_F	slope resistance				1.95	m Ω	
R_{thJC}	thermal resistance junction to case				0.26	K/W	
R_{thCH}	thermal resistance case to heatsink			0.20		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$		481	W	
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$		2.80	kA	
			$V_R = 0\text{ V}$		3.03	kA	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$		2.38	kA	
			$V_R = 0\text{ V}$		2.57	kA	
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$		39.2	kA ² s	
			$V_R = 0\text{ V}$		38.1	kA ² s	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$		28.3	kA ² s	
			$V_R = 0\text{ V}$		27.5	kA ² s	
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		116	pF	

Symbol	Definition	Conditions	Ratings			Unit
			min.	typ.	max.	
I_{RMS}	RMS current	per terminal			200	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				90		g
M_D	mounting torque		2.5		4	Nm
M_T	terminal torque		2.5		4	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	13.0	9.7		mm
$d_{Spb/Appb}$		terminal to backside	16.0	16.0		mm
V_{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA		3600	V
		t = 1 minute			3000	V

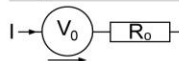


Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDD95-12N1B	MDD95-12N1B	Box	6	453145

Equivalent Circuits for Simulation

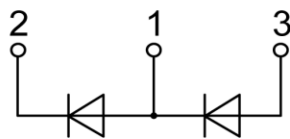
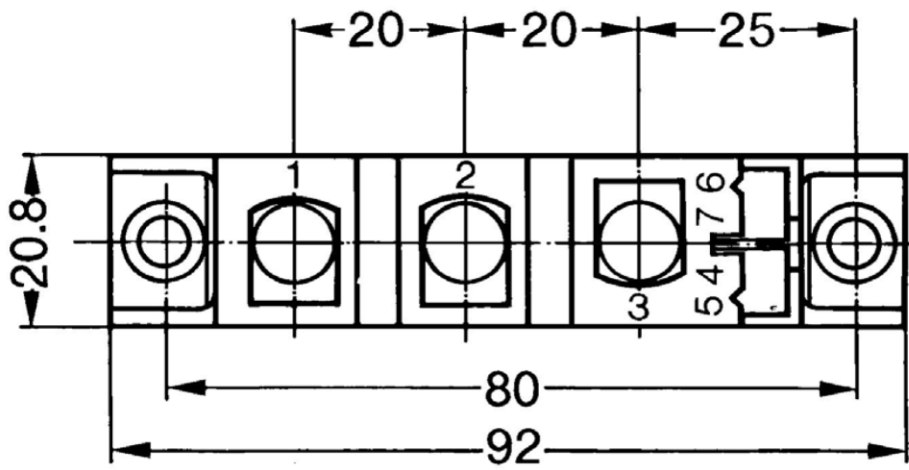
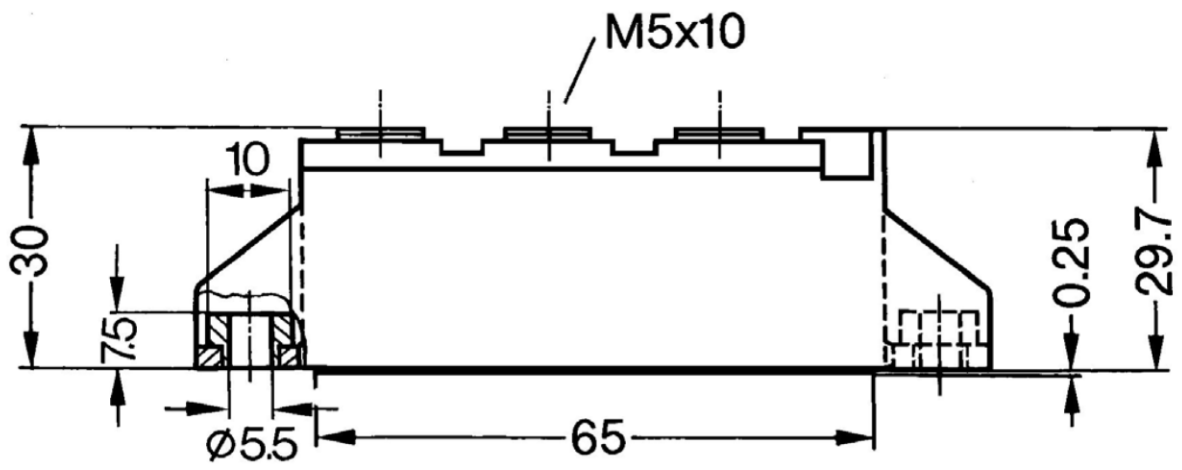
* on die level

$T_{VJ} = 150$ °C



Rectifier

$V_{0\ max}$	threshold voltage	0.75	V
$R_{0\ max}$	slope resistance *	0.76	mΩ



Rectifier

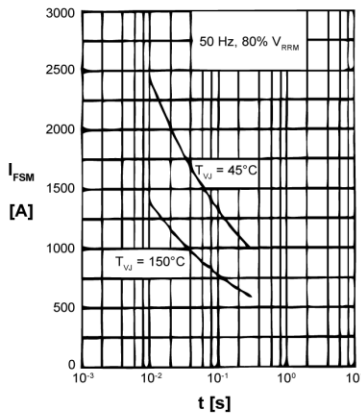


Fig. 1 Surge overload current
 I_{TSM} , I_{FSM} : Crest value, t : duration

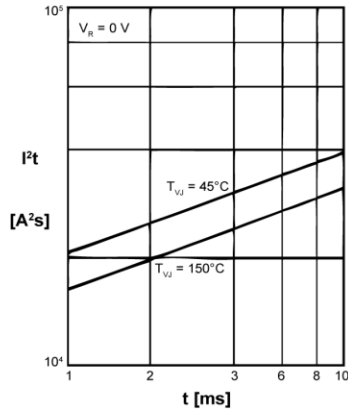


Fig. 2 I^2t versus time (1-10 ms)

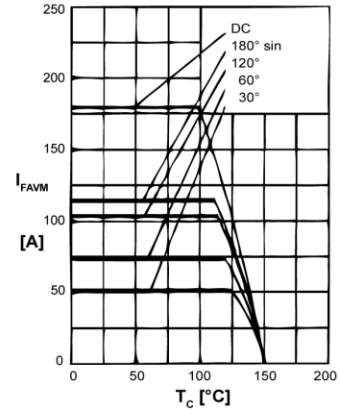


Fig. 3 Maximum forward current at case temperature

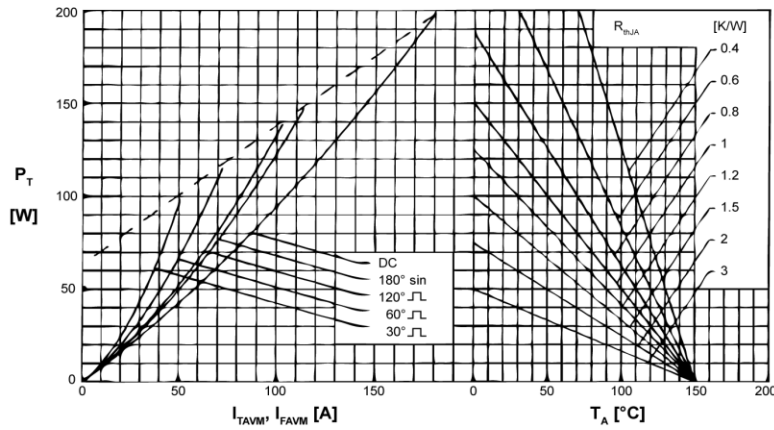


Fig. 4 Power dissipation vs. onstate current and ambient temperature (per diode)

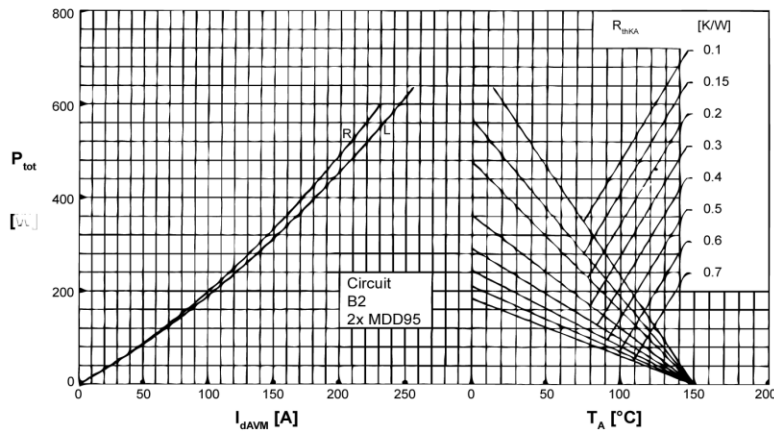


Fig. 6 Single phase rectifier bridge: Power dissipation versus direct output current and ambient temperature; R = resistive load, L = inductive

Rectifier

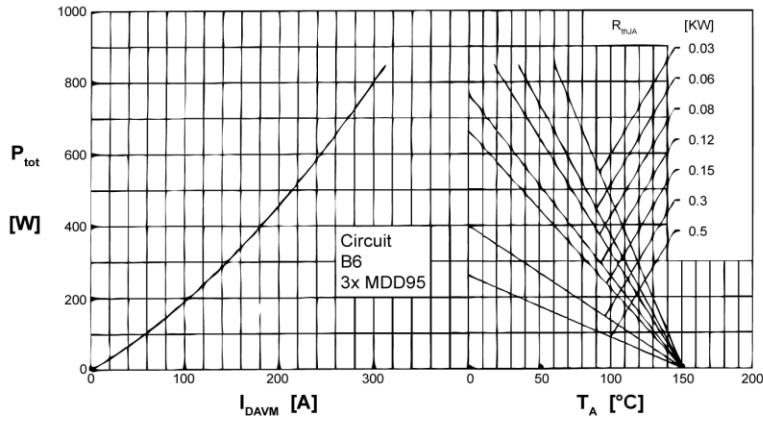


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

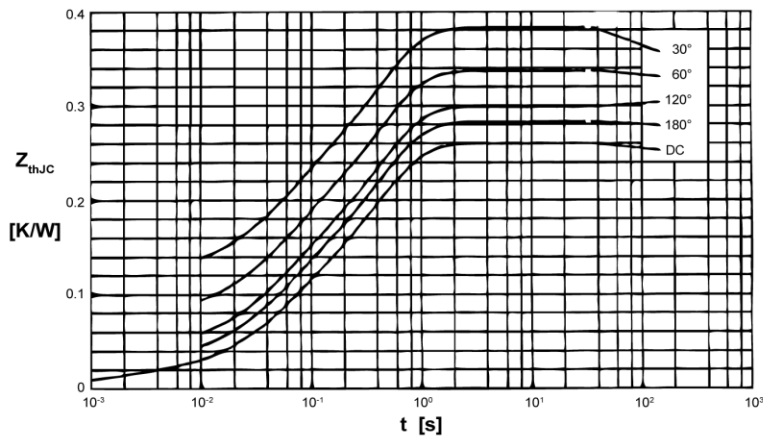


Fig. 7 Transient thermal impedance junction to case (per diode)

R_{thJC} for various conduction angles d:

d	R_{thJC} [K/W]
DC	0.26
180°	0.28
120°	0.30
60°	0.34
30°	0.38

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.013	0.0012
2	0.072	0.0470
3	0.175	0.3940

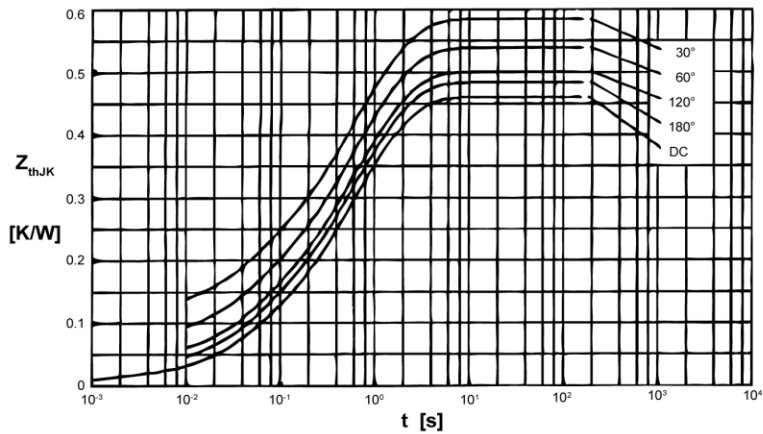


Fig. 8 Transient thermal impedance junction to heatsink (per thyristor)

R_{thJK} for various conduction angles d:

d	R_{thJK} [K/W]
DC	0.46
180°	0.48
120°	0.50
60°	0.54
30°	0.58

Constants for Z_{thJK} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.013	0.0012
2	0.072	0.0470
3	0.175	0.3940
4	0.200	1.3200